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Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, I ² S, POR, PWM, WDT
Number of I/O	18
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VFQFN Exposed Pad
Supplier Device Package	PG-VQFN-24-19
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc1100q024f0008abxuma1

XMC1100

Microcontroller Series
for Industrial Applications

XMC1000 Family

ARM[®] Cortex[™]-M0
32-bit processor core

Data Sheet

V1.4 2014-05

Microcontrollers

XMC1100 Data Sheet

Revision History: V1.4 2014-05

Previous Version: V1.3

Page	Subjects
Page 10	ADC channels of Table 2 is updated. Table 3 is added.
Page 10	Description for Chip Identification Number of Section 1.4 is updated.
Page 17	The pad type is corrected for P1.6 in Table 6.
Page 29	The t_{C12} , f_{C12} , t_{C10} , f_{C10} , t_{C8} and f_{C8} parameters are updated in Table 12.
Page 32	Figure 8 is added.
Page 33	The t_{SR} and t_{TSAL} parameters are updated in Table 13.
Page 36	Parameter name for t_{PSE} is updated. The $N_{WSFLASH}$ parameter and test condition for t_{RET} are added to Table 16.
Page 39	The min value for V_{DDPBO} parameter is added to Table 18. Footnote 1 is updated.
Page 41	The Δf_{LTT} parameter is added to Table 19.
Page 47	Figure 13 is added.

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Summary of Features

- <Z> the package variant
 - T: TSSOP
 - Q: VQFN
- <PPP> package pin count
- <T> the temperature range:
 - F: -40°C to 85°C
 - X: -40°C to 105°C
- <FFFF> the Flash memory size.

For ordering codes for the XMC1100 please contact your sales representative or local distributor.

This document describes several derivatives of the XMC1100 series, some descriptions may not apply to a specific product. Please see [Table 1](#).

For simplicity the term **XMC1100** is used for all derivatives throughout this document.

1.2 Device Types

These device types are available and can be ordered through Infineon's direct and/or distribution channels.

Table 1 Synopsis of XMC1100 Device Types

Derivative	Package	Flash Kbytes	SRAM Kbytes
XMC1100-T016F0008	PG-TSSOP-16-8	8	16
XMC1100-T016F0016	PG-TSSOP-16-8	16	16
XMC1100-T016F0032	PG-TSSOP-16-8	32	16
XMC1100-T016F0064	PG-TSSOP-16-8	64	16
XMC1100-T016X0064	PG-TSSOP-16-8	64	16
XMC1100-T038F0016	PG-TSSOP-38-9	16	16
XMC1100-T038F0032	PG-TSSOP-38-9	32	16
XMC1100-T038F0064	PG-TSSOP-38-9	64	16
XMC1100-T038X0064	PG-TSSOP-38-9	64	16
XMC1100-Q024F0008	PG-VQFN-24-19	8	16
XMC1100-Q024F0016	PG-VQFN-24-19	16	16
XMC1100-Q024F0032	PG-VQFN-24-19	32	16
XMC1100-Q024F0064	PG-VQFN-24-19	64	16
XMC1100-Q040F0016	PG-VQFN-40-13	16	16

Summary of Features

Table 1 Synopsis of XMC1100 Device Types (cont'd)

Derivative	Package	Flash Kbytes	SRAM Kbytes
XMC1100-Q040F0032	PG-VQFN-40-13	32	16
XMC1100-Q040F0064	PG-VQFN-40-13	64	16

1.3 Device Type Features

The following table lists the available features per device type.

Table 2 Features of XMC1100 Device Types¹⁾

Derivative	ADC channel
XMC1100-T016	6
XMC1100-T038	12
XMC1100-Q024	8
XMC1100-Q040	12

1) Features that are not included in this table are available in all the derivatives

Table 3 ADC Channels

Package	VADC0 G0	VADC0 G1
PG-TSSOP-16	CH0..CH5	–
PG-TSSOP-38	CH0..CH7	CH1, CH5 .. CH7
PG-VQFN-24	CH0..CH7	–
PG-VQFN-40	CH0..CH7	CH1, CH5 .. CH7

1.4 Chip Identification Number

The Chip Identification Number allows software to identify the marking. It is a 8 words value with the most significant 7 words stored in Flash configuration sector 0 (CS0) at address location : 1000 0F00_H (MSB) - 1000 0F1B_H (LSB). The least significant word and most significant word of the Chip Identification Number are the value of registers DBGROMID and IDCHIP, respectively.

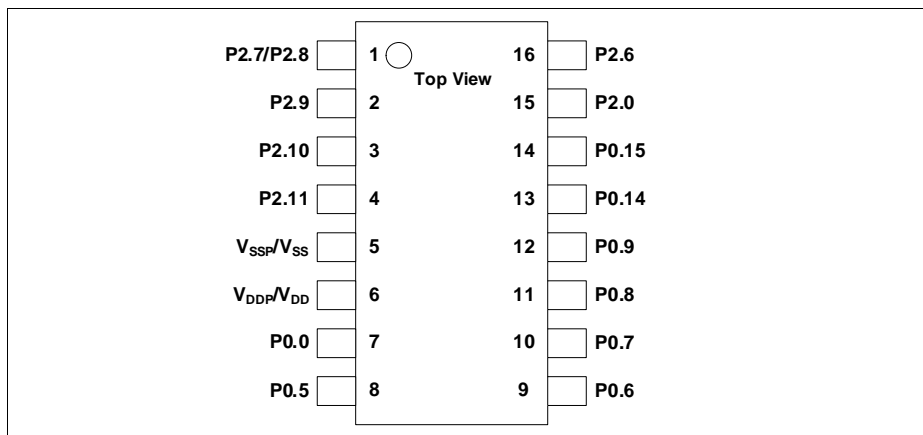


Figure 5 XMC1100 **PG-TSSOP-16** Pin Configuration (top view)

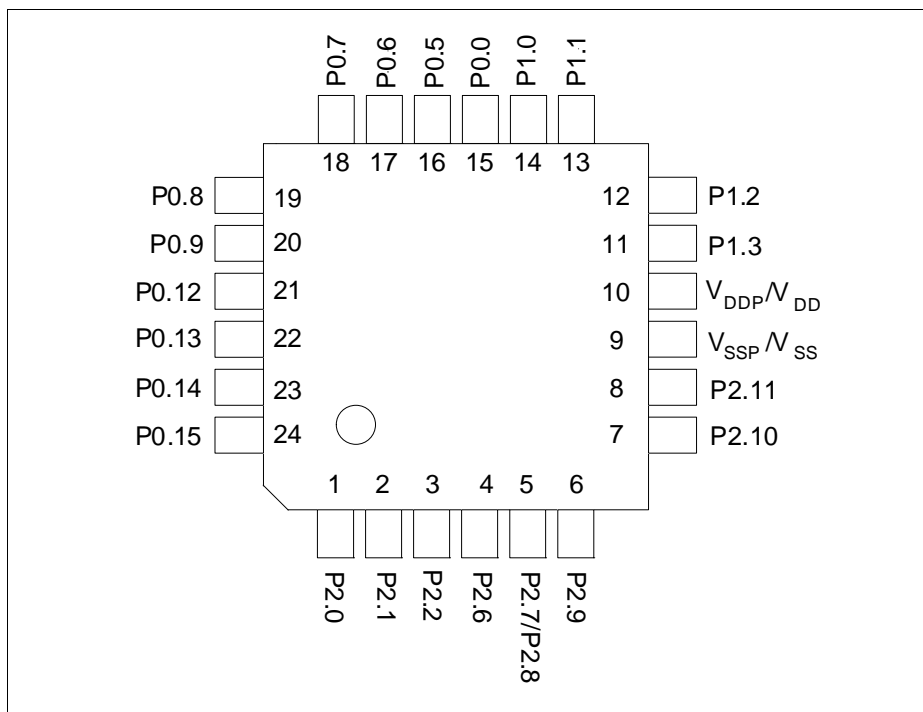


Figure 6 XMC1100 **PG-VQFN-24** Pin Configuration (top view)

General Device Information
Table 6 Package Pin Mapping

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
P0.13	38	32	22	-	STD_INOUT	
P0.14	39	33	23	13	STD_INOUT	
P0.15	40	34	24	14	STD_INOUT	
P1.0	22	16	14	-	High Current	
P1.1	21	15	13	-	High Current	
P1.2	20	14	12	-	High Current	
P1.3	19	13	11	-	High Current	
P1.4	18	12	-	-	High Current	
P1.5	17	11	-	-	High Current	
P1.6	16	-	-	-	STD_INOUT	
P2.0	1	35	1	15	STD_INOUT/AN	
P2.1	2	36	2	-	STD_INOUT/AN	
P2.2	3	37	3	-	STD_IN/AN	
P2.3	4	38	-	-	STD_IN/AN	
P2.4	5	1	-	-	STD_IN/AN	
P2.5	6	2	-	-	STD_IN/AN	
P2.6	7	3	4	16	STD_IN/AN	
P2.7	8	4	5	1	STD_IN/AN	
P2.8	9	5	5	1	STD_IN/AN	
P2.9	10	6	6	2	STD_IN/AN	
P2.10	11	7	7	3	STD_INOUT/AN	
P2.11	12	8	8	4	STD_INOUT/AN	
VSS	13	9	9	5	Power	Supply GND, ADC reference GND
VDD	14	10	10	6	Power	Supply VDD, ADC reference voltage/ ORC reference voltage. VDD has to be supplied with the same voltage as VDDP

Table 8 Port I/O Functions

Function	Outputs									Inputs								
	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	HWO0	HWO1	HWI0	HWI1	Input	Input	Input	Input	Input	Input	Input
P0.0	ERU0. PDOU0		ERU0. GOUT0	CCU40.OUT0		USIC0_CH0. SELO0	USIC0_CH1. SELO0					CCU40.IN0C				USIC0_CH0. DX2A	USIC0_CH1. DX2A	
P0.1	ERU0. PDOU1		ERU0. GOUT1	CCU40.OUT1			SCU_VDROP					CCU40.IN1C						
P0.2	ERU0. PDOU2		ERU0. GOUT2	CCU40.OUT2		VADC0. EMUX02						CCU40.IN2C						
P0.3	ERU0. PDOU3		ERU0. GOUT3	CCU40.OUT3		VADC0. EMUX01						CCU40.IN3C						
P0.4				CCU40.OUT1		VADC0. EMUX00	WWDT. SERVICE_OUT											
P0.5				CCU40.OUT0														
P0.6				CCU40.OUT0		USIC0_CH1. MCLKOUT	USIC0_CH1. DOUT0					CCU40.IN0B				USIC0_CH1. DX0C		
P0.7				CCU40.OUT1		USIC0_CH0. SCLKOUT	USIC0_CH1. DOUT0					CCU40.IN1B				USIC0_CH1. DX1C	USIC0_CH1. DX0D	USIC0_CH1. DX1C
P0.8				CCU40.OUT2		USIC0_CH0. SCLKOUT	USIC0_CH1. SCLKOUT					CCU40.IN2B				USIC0_CH0. DX1B	USIC0_CH1. DX1B	
P0.9				CCU40.OUT3		USIC0_CH0. SELO0	USIC0_CH1. SELO0					CCU40.IN3B				USIC0_CH0. DX2B	USIC0_CH1. DX2B	
P0.10						USIC0_CH0. SELO1	USIC0_CH1. SELO1									USIC0_CH0. DX2C	USIC0_CH1. DX2C	
P0.11				USIC0_CH0. MCLKOUT		USIC0_CH0. SELO2	USIC0_CH1. SELO2									USIC0_CH0. DX2D	USIC0_CH1. DX2D	
P0.12						USIC0_CH0. SELO3						CCU40.IN0A	CCU40.IN1A	CCU40.IN2A	CCU40.IN3A	USIC0_CH0. DX2E		
P0.13	WWDT. SERVICE_OUT					USIC0_CH0. SELO4										USIC0_CH0. DX2F		
P0.14						USIC0_CH0. DOUT0	USIC0_CH0. SCLKOUT									USIC0_CH0. DX0A	USIC0_CH0. DX1A	
P0.15						USIC0_CH0. DOUT0	USIC0_CH1. MCLKOUT									USIC0_CH0. DX0B		
P1.0		CCU40.OUT0					USIC0_CH0. DOUT0		USIC0_CH0. DOUT0		USIC0_CH0. HWIN0					USIC0_CH0. DX0C		
P1.1	VADC0. EMUX00	CCU40.OUT1				USIC0_CH0. DOUT0	USIC0_CH1. SELO0		USIC0_CH0. DOUT1		USIC0_CH0. HWIN1					USIC0_CH0. DX0D	USIC0_CH0. DX1D	USIC0_CH1. DX2E
P1.2	VADC0. EMUX01	CCU40.OUT2					USIC0_CH1. DOUT0		USIC0_CH0. DOUT2		USIC0_CH0. HWIN2					USIC0_CH1. DX0B		
P1.3	VADC0. EMUX02	CCU40.OUT3				USIC0_CH1. SCLKOUT	USIC0_CH1. DOUT0		USIC0_CH0. DOUT3		USIC0_CH0. HWIN3					USIC0_CH1. DX0A	USIC0_CH1. DX1A	
P1.4	VADC0. EMUX10	USIC0_CH1. SCLKOUT				USIC0_CH0. SELO0	USIC0_CH1. SELO1									USIC0_CH0. DX5E	USIC0_CH1. DX5E	
P1.5	VADC0. EMUX11	USIC0_CH0. DOUT0				USIC0_CH0. SELO1	USIC0_CH1. SELO2									USIC0_CH1. DX5F		

Table 8 Port I/O Functions (cont'd)

Function	Outputs									Inputs							
	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	HWO0	HWO1	HWI0	HWI1	Input	Input	Input	Input	Input	Input
P1.6	VADC0. EMUX12	USIC0_CH1.D OUT0		USIC0_CH0.S CLKOUT		USIC0_CH0.S ELO2	USIC0_CH1.S ELO5							USIC0_CH0.D X5F			
P2.0	ERU0. PDOUT3	CCU40.OUT0	ERU0. GOUT3			USIC0_CH0. DOUT0	USIC0_CH0. SCLKOUT						VADC0. G0CH5		ERU0.0B0	USIC0_CH0. DX1E	USIC0_CH0. DX2F
P2.1	ERU0. PDOUT2	CCU40.OUT1	ERU0. GOUT2			USIC0_CH0. DOUT0	USIC0_CH1. SCLKOUT						VADC0. G0CH6		ERU0.1B0	USIC0_CH0. DX3A	USIC0_CH1. DX4A
P2.2													VADC0. G0CH7		ERU0.0B1 DX3A	USIC0_CH0. DX4A	USIC0_CH1. DX5A
P2.3													VADC0. G1CH5		ERU0.1B1	USIC0_CH0. DX5B	USIC0_CH1. DX4C
P2.4													VADC0. G1CH6		ERU0.0A1	USIC0_CH0. DX3B	USIC0_CH1. DX5B
P2.5													VADC0. G1CH7		ERU0.1A1	USIC0_CH0. DX5D	USIC0_CH1. DX4E
P2.6													VADC0. G0CH0		ERU0.2A1	USIC0_CH0. DX3E	USIC0_CH1. DX5D
P2.7													VADC0. G1CH1		ERU0.3A1	USIC0_CH0. DX5C	USIC0_CH1. DX4D
P2.8													VADC0. G0CH1	VADC0. G1CH0	ERU0.3B1	USIC0_CH0. DX3D	USIC0_CH0. DX4D
P2.9													VADC0. G0CH2	VADC0. G1CH4	ERU0.3B0	USIC0_CH0. DX5A	USIC0_CH1. DX4B
P2.10	ERU0. PDOUT1	CCU40.OUT2	ERU0. GOUT1				USIC0_CH1. DOUT0						VADC0. G0CH3	VADC0. G1CH2	ERU0.2B0	USIC0_CH0. DX3C	USIC0_CH0. DX4C
P2.11	ERU0. PDOUT0	CCU40.OUT3	ERU0. GOUT0			USIC0_CH1. SCLKOUT	USIC0_CH1. DOUT0						VADC0. G0CH4	VADC0. G1CH3	ERU0.2B1	USIC0_CH1. DX0E	USIC0_CH1. DX1E

3 Electrical Parameter

This section provides the electrical parameter which are implementation-specific for the XMC1100.

3.1 General Parameters

3.1.1 Parameter Interpretation

The parameters listed in this section represent partly the characteristics of the XMC1100 and partly its requirements on the system. To aid interpreting the parameters easily when evaluating them for a design, they are indicated by the abbreviations in the "Symbol" column:

- **CC**
Such parameters indicate **C**ontroller **C**haracteristics, which are distinctive feature of the XMC1100 and must be regarded for a system design.
- **SR**
Such parameters indicate **S**ystem **R**equirements, which must be provided by the application system in which the XMC1100 is designed in.

3.1.3 Operating Conditions

The following operating conditions must not be exceeded in order to ensure correct operation and reliability of the XMC1100. All parameters specified in the following tables refer to these operating conditions, unless noted otherwise.

Table 10 Operating Conditions Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Ambient Temperature	T_A SR	-40	–	85	°C	Temp. Range F
		-40	–	105	°C	Temp. Range X
Digital supply voltage ¹⁾	V_{DDP} SR	1.8	–	5.5	V	
MCLK Frequency	f_{MCLK} CC	–	–	33.2	MHz	CPU clock
PCLK Frequency	f_{PCLK} CC	–	–	66.4	MHz	Peripherals clock

1) See also the Supply Monitoring thresholds, [Chapter 3.3.3](#).

Electrical Parameter
Table 11 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Input high voltage on port pins (Large Hysteresis)	V_{IHPL}	SR	$0.85 \times V_{DDP}$	—	V	CMOS Mode (5 V, 3.3 V & 2.2 V) ³⁾
Input Hysteresis ¹⁾	HYS	CC	$0.08 \times V_{DDP}$	—	V	CMOS Mode (5 V), Standard Hysteresis
			$0.03 \times V_{DDP}$	—	V	CMOS Mode (3.3 V), Standard Hysteresis
			$0.02 \times V_{DDP}$	—	V	CMOS Mode (2.2 V), Standard Hysteresis
			$0.5 \times V_{DDP}$	$0.75 \times V_{DDP}$	V	CMOS Mode(5 V), Large Hysteresis
			$0.4 \times V_{DDP}$	$0.75 \times V_{DDP}$	V	CMOS Mode(3.3 V), Large Hysteresis
			$0.2 \times V_{DDP}$	$0.65 \times V_{DDP}$	V	CMOS Mode(2.2 V), Large Hysteresis
Pull-up resistor on port pins	R_{PUP}	CC	20	50	kohm	$V_{IN} = V_{SSP}$
Pull-down resistor on port pins	R_{PDP}	CC	20	50	kohm	$V_{IN} = V_{DDP}$
Input leakage current ²⁾	I_{OZP}	CC	-1	1	μA	$0 < V_{IN} < V_{DDP}$, $T_A \leq 105^\circ\text{C}$
Overload current on any pin	I_{OVP}	SR	-5	5	mA	
Absolute sum of overload currents	$\Sigma I_{OVP} $	SR	—	25	mA	³⁾
Voltage on any pin during V_{DDP} power off	V_{PO}	SR	—	0.3	V	⁴⁾
Maximum current per pin (excluding P1, V_{DDP} and V_{SS})	I_{MP}	SR	-10	11	mA	—
Maximum current per high current pins	I_{MP1A}	SR	-10	50	mA	—

Electrical Parameter
Table 12 ADC Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gain settings	G_{IN} CC	1			–	GNCTRxz.GAINy = 00 _B (unity gain)
		3			–	GNCTRxz.GAINy = 01 _B (gain g1)
		6			–	GNCTRxz.GAINy = 10 _B (gain g2)
		12			–	GNCTRxz.GAINy = 11 _B (gain g3)
Sample Time	t_{sample} CC	3	–	–	1 / f_{ADC}	$V_{DDP} = 5.0$ V
		3	–	–	1 / f_{ADC}	$V_{DDP} = 3.3$ V
		30	–	–	1 / f_{ADC}	$V_{DDP} = 1.8$ V
Sigma delta loop hold time	t_{SD_hold} CC	20	–	–	μs	Residual charge stored in an active sigma delta loop remains available
Conversion time in fast compare mode	t_{CF} CC	9			1 / f_{ADC}	2)
Conversion time in 12-bit mode	t_{C12} CC	20			1 / f_{ADC}	2)
Maximum sample rate in 12-bit mode ³⁾	f_{C12} CC	–	–	$f_{ADC} / 42.5$	–	1 sample pending
		–	–	$f_{ADC} / 62.5$	–	2 samples pending
Conversion time in 10-bit mode	t_{C10} CC	18			1 / f_{ADC}	2)
Maximum sample rate in 10-bit mode ³⁾	f_{C10} CC	–	–	$f_{ADC} / 40.5$	–	1 sample pending
		–	–	$f_{ADC} / 58.5$	–	2 samples pending
Conversion time in 8-bit mode	t_{C8} CC	16			1 / f_{ADC}	2)

3.2.4 Power Supply Current

The total power supply current defined below consists of a leakage and a switching component.

Application relevant values are typically lower than those given in the following tables, and depend on the customer's system operating conditions (e.g. thermal connection or used application configurations).

Table 14 Power Supply Parameters¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ. ²⁾	Max.		
Active mode current ³⁾	I_{DDPA} CC	–	8.4	11.0	mA	$f_{MCLK} = 32 \text{ MHz}$ $f_{PCLK} = 64 \text{ MHz}$
		–	3.7	–	mA	$f_{MCLK} = 1 \text{ MHz}$ $f_{PCLK} = 1 \text{ MHz}$
Sleep mode current Peripherals clock enabled ⁴⁾	I_{DDPSE} CC	–	5.9	–	mA	$f_{MCLK} = 32 \text{ MHz}$ $f_{PCLK} = 64 \text{ MHz}$
Sleep mode current Peripherals clock disabled ⁵⁾	I_{DDPSD} CC	–	1.2	–	mA	$f_{MCLK} = 1 \text{ MHz}$ $f_{PCLK} = 1 \text{ MHz}$
Deep Sleep mode current ⁶⁾	I_{DDPDS} CC	–	0.24	–	mA	
Wake-up time from Sleep to Active mode ⁷⁾	t_{SSA} CC	–	6	–	cycles	
Wake-up time from Deep Sleep to Active mode ⁸⁾	t_{DSA} CC	–	280	–	μsec	

1) Not all parameters are 100% tested, but are verified by design/characterisation and test correlation.

2) The typical values are measured at $T_A = +25^\circ\text{C}$ and $V_{DDP} = 5 \text{ V}$.

3) CPU and all peripherals clock enabled, Flash is in active mode.

4) CPU is sleep, all peripherals clock enabled and Flash is in active mode.

5) CPU is sleep, Flash is powered down and code executed from RAM after wake-up.

6) CPU is sleep, peripherals clock disabled, Flash is powered down and code executed from RAM after wake-up.

7) CPU is sleep, Flash is in active mode during sleep mode.

8) CPU is sleep, Flash is in power down mode during deep sleep mode.

Electrical Parameter

Table 15 provides the active current consumption of some modules operating at 5 V power supply at 25 °C. The typical values shown are used as a reference guide on the current consumption when these modules are enabled.

Table 15 Typical Active Current Consumption¹⁾

Active Current Consumption	Symbol	Limit Values	Unit	Test Condition
		Typ.		
Baseload current	I_{CPUDDC}	5.04	mA	Modules including Core, SCU, PORT, memories, ANATOP ²⁾
VADC and SHS	I_{ADCDDC}	3.4	mA	Set CGATCLR0.VADC to 1 ³⁾
USIC0	$I_{USIC0DDC}$	0.87	mA	Set CGATCLR0.USIC0 to 1 ⁴⁾
CCU40	$I_{CCU40DDC}$	0.94	mA	Set CGATCLR0.CCU40 to 1 ⁵⁾
WDT	I_{WDTDDC}	0.03	mA	Set CGATCLR0.WDT to 1 ⁶⁾
RTC	I_{RTCDDC}	0.01	mA	Set CGATCLR0.RTC to 1 ⁷⁾

1) Not subject to production test, verified by design/characterisation.

2) Baseload current is measured with device running in user mode, MCLK=PCLK=32 MHz, with an endless loop in the flash memory. The clock to the modules stated in CGATSTAT0 are gated.

3) Active current is measured with: module enabled, MCLK=32 MHz, running in auto-scan conversion mode

4) Active current is measured with: module enabled, alternating messages sent to PC at 57.6kbaud every 200ms

5) Active current is measured with: module enabled, MCLK=PCLK=32 MHz, 1 CCU4 slice for PWM switching from 1500Hz and 1000Hz at regular intervals, 1 CCU4 slice in capture mode for reading period and duty cycle

6) Active current is measured with: module enabled, MCLK=32 MHz, time-out mode; WLB = 0, WUB = 0x00008000; WDT serviced every 1s

7) Active current is measured with: module enabled, MCLK=32 MHz, Periodic interrupt enabled

3.3.2 Output Rise/Fall Times

Table 17 provides the characteristics of the output rise/fall times in the XMC1100. **Figure 9** describes the rise time and fall time parameters.

Table 17 Output Rise/Fall Times Parameters (Operating Conditions apply)

Parameter	Symbol	Limit Values		Unit	Test Conditions
		Min.	Max.		
Rise/fall times on High Current Pad ¹⁾²⁾	t_{HCPR} , t_{HCPF}	—	9	ns	50 pF @ 5 V ³⁾
		—	12	ns	50 pF @ 3.3 V ⁴⁾
		—	25	ns	50 pF @ 1.8 V ⁵⁾
Rise/fall times on Standard Pad ¹⁾²⁾	t_R , t_F	—	12	ns	50 pF @ 5 V ⁶⁾
		—	15	ns	50 pF @ 3.3 V ⁷⁾
		—	31	ns	50 pF @ 1.8 V ⁸⁾

1) Rise/Fall time parameters are taken with 10% - 90% of supply.

2) Not all parameters are 100% tested, but are verified by design/characterisation and test correlation.

3) Additional rise/fall time valid for $C_L = 50$ pF - $C_L = 100$ pF @ 0.150 ns/pF at 5 V supply voltage.

4) Additional rise/fall time valid for $C_L = 50$ pF - $C_L = 100$ pF @ 0.205 ns/pF at 3.3 V supply voltage.

5) Additional rise/fall time valid for $C_L = 50$ pF - $C_L = 100$ pF @ 0.445 ns/pF at 1.8 V supply voltage.

6) Additional rise/fall time valid for $C_L = 50$ pF - $C_L = 100$ pF @ 0.225 ns/pF at 5 V supply voltage.

7) Additional rise/fall time valid for $C_L = 50$ pF - $C_L = 100$ pF @ 0.288 ns/pF at 3.3 V supply voltage.

8) Additional rise/fall time valid for $C_L = 50$ pF - $C_L = 100$ pF @ 0.588 ns/pF at 1.8 V supply voltage.

3.3.7.2 Inter-IC (IIC) Interface Timing

The following parameters are applicable for a USIC channel operated in IIC mode.

Note: Operating Conditions apply.

Table 25 USIC IIC Standard Mode Timing¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	t_1 CC/SR	-	-	300	ns	
Rise time of both SDA and SCL	t_2 CC/SR	-	-	1000	ns	
Data hold time	t_3 CC/SR	0	-	-	µs	
Data set-up time	t_4 CC/SR	250	-	-	ns	
LOW period of SCL clock	t_5 CC/SR	4.7	-	-	µs	
HIGH period of SCL clock	t_6 CC/SR	4.0	-	-	µs	
Hold time for (repeated) START condition	t_7 CC/SR	4.0	-	-	µs	
Set-up time for repeated START condition	t_8 CC/SR	4.7	-	-	µs	
Set-up time for STOP condition	t_9 CC/SR	4.0	-	-	µs	
Bus free time between a STOP and START condition	t_{10} CC/SR	4.7	-	-	µs	
Capacitive load for each bus line	C_b SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximately 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

Table 26 USIC IIC Fast Mode Timing ¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	t_1 CC/SR	20 + 0.1 * C_b ²⁾	-	300	ns	
Rise time of both SDA and SCL	t_2 CC/SR	20 + 0.1 * C_b	-	300	ns	
Data hold time	t_3 CC/SR	0	-	-	µs	
Data set-up time	t_4 CC/SR	100	-	-	ns	
LOW period of SCL clock	t_5 CC/SR	1.3	-	-	µs	
HIGH period of SCL clock	t_6 CC/SR	0.6	-	-	µs	
Hold time for (repeated) START condition	t_7 CC/SR	0.6	-	-	µs	
Set-up time for repeated START condition	t_8 CC/SR	0.6	-	-	µs	
Set-up time for STOP condition	t_9 CC/SR	0.6	-	-	µs	
Bus free time between a STOP and START condition	t_{10} CC/SR	1.3	-	-	µs	
Capacitive load for each bus line	C_b SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximately 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

2) C_b refers to the total capacitance of one bus line in pF.

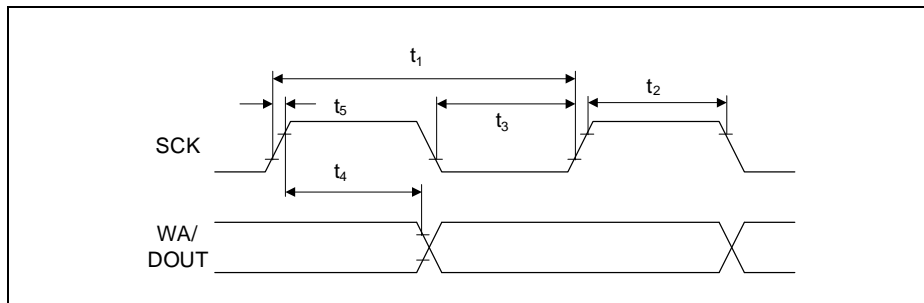


Figure 17 USIC IIS Master Transmitter Timing

Table 28 USIC IIS Slave Receiver Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_6 SR	$4/f_{MCLK}$	-	-	ns	
Clock HIGH	t_7 SR	$0.35 \times t_{6min}$	-	-	ns	
Clock Low	t_8 SR	$0.35 \times t_{6min}$	-	-	ns	
Set-up time	t_9 SR	$0.2 \times t_{6min}$	-	-	ns	
Hold time	t_{10} SR	10	-	-	ns	

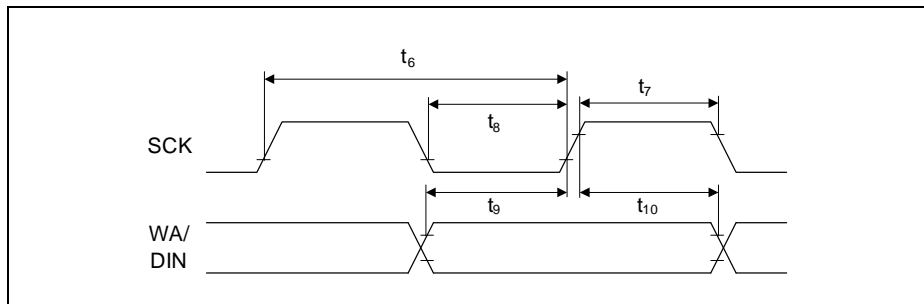


Figure 18 USIC IIS Slave Receiver Timing

4 Package and Reliability

The XMC1100 is a member of the XMC1000 Derivatives of microcontrollers. It is also compatible to a certain extent with members of similar families or subfamilies.

Each package is optimized for the device it houses. Therefore, there may be slight differences between packages of the same pin-count but for different device types. In particular, the size of the exposed die pad may vary.

If different device types are considered or planned for an application, it must be ensured that the board layout fits all packages under consideration.

4.1 Package Parameters

Table 29 provides the thermal characteristics of the packages used in XMC1100.

Table 29 Thermal Characteristics of the Packages

Parameter	Symbol	Limit Values		Unit	Package Types
		Min.	Max.		
Exposed Die Pad Dimensions	Ex × Ey CC	-	2.7 × 2.7	mm	PG-VQFN-24-19
		-	3.7 × 3.7	mm	PG-VQFN-40-13
Thermal resistance Junction-Ambient	$R_{\Theta JA}$ CC	-	104.6	K/W	PG-TSSOP-16-8 ¹⁾
		-	70.3	K/W	PG-TSSOP-38-9 ¹⁾
		-	46.0	K/W	PG-VQFN-24-19 ¹⁾
		-	38.4	K/W	PG-VQFN-40-13 ¹⁾

1) Device mounted on a 4-layer JEDEC board (JESD 51-5); exposed pad soldered.

Note: For electrical reasons, it is required to connect the exposed pad to the board ground V_{SSP} , independent of EMC and thermal requirements.

4.1.1 Thermal Considerations

When operating the XMC1100 in a system, the total heat generated in the chip must be dissipated to the ambient environment to prevent overheating and the resulting thermal damage.

The maximum heat that can be dissipated depends on the package and its integration into the target board. The “Thermal resistance $R_{\Theta JA}$ ” quantifies these parameters. The power dissipation must be limited so that the average junction temperature does not exceed 115 °C.

The difference between junction temperature and ambient temperature is determined by $\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta JA}$

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